

# Ba<sub>0.5</sub>Sr<sub>0.5</sub>TiO<sub>3</sub> based Photodiode Application as Light Sensor for Automatic Lighting Control Switch

*by* Budi Harsono

---

**Submission date:** 16-Apr-2023 03:29PM (UTC+0700)

**Submission ID:** 2065747167

**File name:** 76-Budi\_Harsono-Ba0.5Sr0.5TiO3\_Based\_Photodiode\_Application.pdf (291.92K)

**Word count:** 1705

**Character count:** 8848

# Ba<sub>0.5</sub>Sr<sub>0.5</sub>TiO<sub>3</sub> Based Photodiode Application As Light Sensor for Automatic Lighting Control Switch

Budi Harsono<sup>1</sup>, Johansah Liman<sup>1</sup>, Johan Iskandar<sup>2</sup>, Eti Rohaeti<sup>3</sup>, Irzaman<sup>4</sup>

**Abstract**— Photodiode that was made from ferroelectric material, Barium Strontium Titanate (BST), was used as light sensor for automatic lighting control switch. BST photodiode was put in the wheatstone bridge and difference amplifier circuit was used to enhance the sensitivity of BST sensor. Output voltage of the difference amplifier was then passed to the voltage comparator circuit to get the logic output for the lighting control. BC548 general purpose transistor was used for control the relay to turn on and turn off a fluorescent lamp. The experiment result shown that BST based photodiode been able to used as light sensor for automatic lighting control switch applications.

**Keywords**— automatic switch, BST, difference amplifier, light sensor, photodiode.

## I. INTRODUCTION

FERROELECTRIC thin films are potentially important materials for a variety of devices such as ferroelectric memories, infrared pyroelectric sensors and in other integrated technologies. Barium strontium titanate (BST) is currently one of the most interesting ferroelectric materials due to its high dielectric constant and composition-dependent Curie temperatur [1].

Barium Strontium Titanate (Ba<sub>x</sub>Sr<sub>1-x</sub>TiO<sub>3</sub>) being environment friendly, has high dielectric constant, low dissipation factor, compositional-dependent Curie temperature (T<sub>c</sub>) and large electro-optical coefficient [2]. The outstanding properties of perovskite oxides such as barium strontium titanate (BST) have recently aroused great interest with regard to their application as functional material for the development of chemical sensors and biosensors [3].

BST thin film can be created with a number of techniques, e.g. Chemical Solution Deposition (CSD), Pulsed Laser

Deposition (PLD), sputtering and Metallo Organic Chemical Vapour Deposition (MOCVD) [4-6]. It has been demonstrated that Ba<sub>0.5</sub>Sr<sub>0.5</sub>TiO<sub>3</sub> thin films were prepared by the CSD method on the substrate Si (100) p-type substrate can work as a light sensor and had photo diode characteristic [7, 8].

The purpose of this study is using Ba<sub>0.5</sub>Sr<sub>0.5</sub>TiO<sub>3</sub> based photodiode as a light sensor for automatic lighting control switch.

## II. EXPERIMENTAL METHOD

In this study, BST thin film was grown on p-type silicon (100) substrate using Chemical Solution Deposition (CSD) method. The materials used in this experiment were Barium asetat powder [Ba(CH<sub>3</sub>COO)<sub>2</sub>] (99%), Strontium asetat powder [Sr(CH<sub>3</sub>COO)<sub>2</sub>] (99%), Titanium dioxide powder [TiO<sub>2</sub>] (97.999%), and 2-Methoxy ethanol solvent [H<sub>3</sub>COCH<sub>2</sub>CH<sub>2</sub>OH] (99%). All the materials were obtained from Sigma Aldrich.

First, the Silicon substrate was cut to the size of 1x1 cm<sup>2</sup> using a glass cutter. The substrate was then washed with aqua bidest distilled water for 30 seconds. Then the materials necessary (barium acetate, strontium acetate, and titanium dioxide) were weighed using Sartorius BL6100 analytical balance. Molar fraction of Ba and Sr was 0.5. The materials were then mixed and dissolved in 2.5 ml of 2-Methoxy ethanol. Furthermore, the solution that has been made was homogenized with Branson 2510 ultrasonicator for 90 minutes to obtain a homogeneous BST solution.

BST solution which has been homogeneous then dripped on the p-type silicon substrate and spun using a spin coater 30 seconds at a speed of 3000 rpm. BST coating process on p-type silicon (100) substrate is repeated 5 times with one minute in-between breaks. BST thin film on p-type silicon (100) substrate then annealed using Vulcan<sup>TM-3000</sup> furnace for 22 hours at 850 °C temperature.

The next process was the contact deposition process. BST film that have been annealed were covered with aluminum foil with four square holes of 2x2 mm<sup>2</sup> in the part to be fitted with contact. The material used as a contact in this study was aluminium 99.999%. The deposition process was conducted using Metal Oxide Chemical Vapor Deposition (MOCVD) method.

Manuscript received August 28, 2015. This work was funded by the Pekerti Grant, Coordination of Private Tertiary School Region III, Ministry of Education and Culture, Republic of Indonesia under contract No. 095/K3/KM/2015.

<sup>1</sup> Lecturer on Electrical Engineering Department, Faculty of Engineering and Computer Science, Krida Wacana Christian University, Jakarta, Indonesia (phone: ; fax: ; email:budi.harsono@ukrida.ac.id,johansah@ukrida.ac.id)

<sup>2</sup> Postgraduate Student on Physics Departement, FMIPA, IPB, Bogor, Indonesia

<sup>3</sup> Lecturer on Chemical Departement, FMIPA, IPB, Bogor, Indonesia

<sup>4</sup> Lecturer on Physics Departement, FMIPA, IPB, Bogor, Indonesia

The next step was building the wheatstone bridge and difference amplifier circuit to increase the sensitivity of the BST light sensor. The circuit is shown in Figure 1. The wheatstone bridge output ( $V_1-V_2$ ) was adjusted at 0V in very dark condition (at about 2 lux light intensity). Output from difference amplifier can be obtained from Equation 1 and internal resistance of BST sensor can be obtained from Equation 2.

$$V_{out1} = \frac{R_f}{R_i} (V_1 - V_2) \quad (1)$$

with:  $R_4 = R_6 = R_f$   
 $R_3 = R_5 = R_i$

$$R_{BST} = \frac{R_1(V_2 - V_1)}{V_1} \quad (2)$$

The output of the difference amplifier was then passed to the voltage comparator circuit to obtain a discrete output that distinguishes the dark and light conditions. Voltage comparator circuit was shown in Figure 2.  $V_{ref}$  was adjusted at 1.5 volt, so the output voltage ( $V_{out2}$ ) will be logic 'high' when  $V_{out1}$  below 1.5 volt.

The output of the voltage comparator was then used to drive a relay through the driver transistor, so that when conditions are dark, the fluorescent lamp will turn on and during bright conditions, the lamp will turn off. The relay circuit is shown in Figure 3.

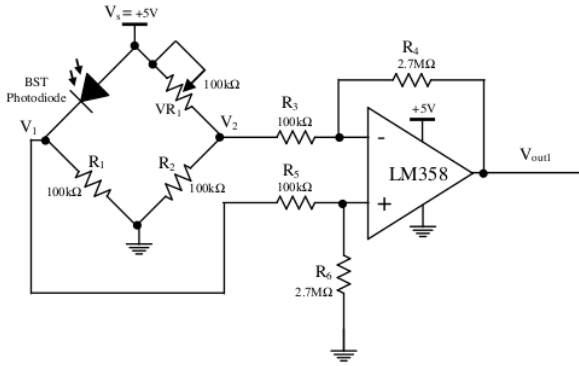


Fig. 1. Wheatstone bridge and difference amplifier circuit.

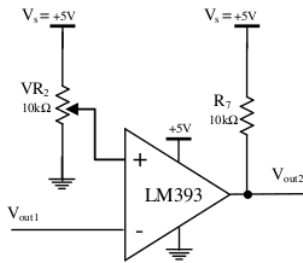


Fig. 2. Voltage comparator circuit.

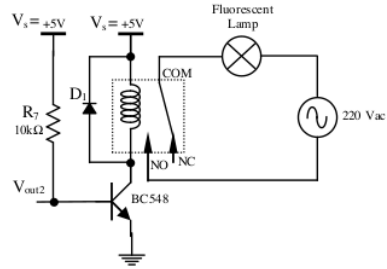


Fig. 3. Relay driver circuit.

### III. RESULTS AND DISCUSSION

The output voltage of the Wheatstone bridge circuit ( $V_1-V_2$ ) measured in several levels of light intensity are given in Table 1. The results shown that when light intensity is increase, internal resistance of BST light sensor is decrease, resulting output voltage of the wheatstone bridge circuit to increase. Curve pattern of the BST internal resistance is shown in Figure 4.

Output voltage from the difference amplifier circuit are given in Table 2 and output voltage from voltage comparator circuit are given in Table 3. Difference amplifier output voltage shown that the amplification of difference amplifier circuit is 27x and voltage comparator output shown that when light intensity is 100 lux or lower, outputs of the voltage comparator are logic 'high' (=4.948 volt) and when the light intensity is 150 lux or higher, outputs of the voltage comparator are logic 'low' (0.054 volt).

TABLE I  
WHEATSTONE BRIDGE OUTPUT VOLTAGE

Light Intensity (lux)	$V_1 - V_2$ (volt)
50	0.006
100	0.036
150	0.06
200	0.08
250	0.09
300	0.098
350	0.108
400	0.12

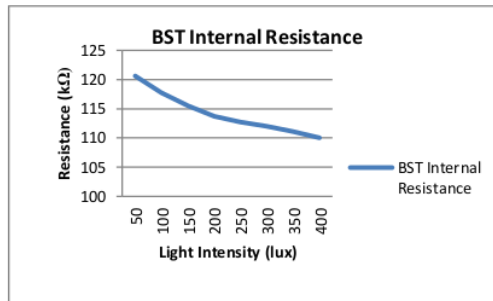


Fig. 4. BST Internal Resistance

TABLE II  
DIFFERENCE AMPLIFIER OUTPUT VOLTAGE

$V_1 - V_2$ (volt)	$V_{out1}$ (volt)	Amplification (x)
0.006	0.162	27
0.036	0.97	26.94444
0.06	1.62	27
0.08	2.161	27.0125
0.09	2.43	27
0.098	2.647	27.0102
0.108	2.915	26.99074
0.12	3.242	27.01667

TABLE III  
VOLTAGE COMPARATOR OUTPUT VOLTAGE

Light Intensity (lux)	$V_{out1}$ (volt)	$V_{out2}$ (volt)
50	0.162	4.948
100	0.97	4.948
150	1.62	0.054
200	2.161	0.054
250	2.43	0.054
300	2.647	0.054
350	2.915	0.054
400	3.242	0.054

TABLE IV  
OVERALL TEST RESULTS

Light intensity	Lamp condition
Dark condition (<135 lux)	ON
Light condition ( $\geq$ 135 lux)	OFF

Overall test results are shown in Table 4. From the overall test results, we obtained that lamp will turn on when high intensity is below 135 lux (dark condition) and will turn off when light intensity is 135 lux or higher (light condition).

#### IV. CONCLUSION

The change of the internal resistance of the BST sensor is very small, so the output voltage of the wheatstone bridge circuit need to be amplified by difference amplifier to achieve an applicable output voltage. From the overall test result, Barium Strontium Titanate ( $Ba_{0.5}Sr_{0.5}TiO_3$ ) based photodiode was successfully used as a light sensor for automatic lighting control switch.

#### REFERENCES

- [1] F. M. Pontes, E. R. Leite, D. S. L. Pontes, E. Longo, E. M. S. Santos, S. Mergulha<sup>o</sup>, P. S. Pizani, F. Lanciotti, Jr., and T. M. Boschi, and J. A. Varela, "Ferroelectric and optical properties of  $Ba_{0.8}Sr_{0.2}TiO_3$  thin film," *Journal of Applied Physics*, Vol.91, No.2, pp. 5972-5978, May 2002.
- [2] K. Anumeet, S. Anupinder, K.Asokan, S. Lakhwant, "Structural and Optical Properties of Iron Doped Barium Strontium Titanate," *IJEAR*, Vol.4, No.2, Spl-1, July - Dec 2014.
- [3] C. Huck, A. Poghossian, M. Bäcker, S. Reisert, J. Schubert, W. Zander, V.K. Begoyan, V.V. Buniatyan, M.J. Schöning, "Chemical sensors based on a high- $k$  perovskite oxide of barium strontium titanate," in *Procedia Engineering* 87, pp.28–31, 2014.
- [4] Y. Xin, R.Wei, S. Peng,W. Xiaoqing, and Y. Xi, "Enhanced Tunable Dielectric Properties Of  $Ba_{0.5}Sr_{0.5}TiO_3/ Bi_{1.5}Zn_{1.0}Nb_{1.5}O_7$  Multilayer Thin Films By A Sol-Gel Process," *Thin Solid Films*, Vol.520, No. 2, pp. 789–792, 2011.
- [5] A. W. Nuayi, H. Alatas, Irzaman, dan M. Rahmat, "Enhancement of Photon Absorption on  $Ba_xSr_{1-x}TiO_3$  Thin-Film Semiconductor Using Photonic Crystal," *International Journal of Optics*, 2014.
- [6] Umar, Faanzir, A. W. Nuayi, R. Siskandar, H. Syafutra, H. Alatas, and Irzaman, "Characterization of optical properties of  $Ba_{0.55}Sr_{0.45}TiO_3$  Thin Film" in *SNIPD Symposium Proceeding*, ITB Bandung, pp. 280-284, 2013.
- [7] J. Iskandar, H. Syafutra, J. Juansah, dan Irzaman, "Characterizations of electrical and optical properties on ferroelectric photodiode of barium strontium titanate ( $Ba_{0.5}Sr_{0.5}TiO_3$ ) films based on the annealing time differences and its development as light sensor on satellite technology," *Procedia Environmental Sciences* 24, pp.324 – 328, 2015.
- [8] J. Liman, B. Harsono, A. Kurniawan, E. Rohaeti, Irzaman, "Making Photodiode Based on  $Ba_{0.5}Sr_{0.5}TiO_3$  Thin Film on Type-p Si (100) Substrate with Chemical Solution Deposition (CSD) Method," unpublished.

# Ba<sub>0.5</sub>Sr<sub>0.5</sub>TiO<sub>3</sub> based Photodiode Application as Light Sensor for Automatic Lighting Control Switch

## ORIGINALITY REPORT

15%

SIMILARITY INDEX

8%

INTERNET SOURCES

11%

PUBLICATIONS

6%

STUDENT PAPERS

## PRIMARY SOURCES

- 1 Shi, P.. "Preparation and properties of (Ba<sub>0.7</sub>Sr<sub>0.3</sub>)TiO<sub>3</sub> thin films by soft-solution processing", *Journal of Crystal Growth*, 20050315  
Publication 3%
- 2 Submitted to Institut Pertanian Bogor  
Student Paper 3%
- 3 cyberleninka.org  
Internet Source 3%
- 4 Johan Iskandar, Heriyanto Syafutra, Jajang Juansah, Irzaman. "Characterizations of Electrical and Optical Properties on Ferroelectric Photodiode of Barium Strontium Titanate (Ba<sub>0.5</sub>Sr<sub>0.5</sub>TiO<sub>3</sub>) Films Based on the Annealing Time Differences and its Development as Light Sensor on Satellite Technology", *Procedia Environmental Sciences*, 2015  
Publication 1%

5	Microelectronics International, Volume 29, Issue 3 (2012-07-28) Publication	1 %
6	Submitted to UIN Sunan Kalijaga Yogyakarta Student Paper	1 %
7	Yang, C.H.. "Fabrication and properties of silicon-based (Bi,Sm) <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> thin film", Journal of Alloys and Compounds, 20090107 Publication	1 %
8	simakip.uhamka.ac.id Internet Source	1 %
9	www.hindawi.com Internet Source	1 %
10	Xin Yan, Wei Ren, Peng Shi, Xiaoqing Wu, Xiaofeng Chen, Xi Yao. " Structures and Tunability of Ba Sr TiO /Bi Zn Nb O Multilayer Thin Films Grown on Pt/Al O Substrates ", Ferroelectrics, 2009 Publication	1 %
11	Irzaman, Heriyanto Syafutra, Endang Rancasa, Abdul Wahidin Nuayi et al. " The Effect of Ba/Sr Ratio on Electrical and Optical Properties of Ba Sr TiO (x = 0.25; 0.35; 0.45; 0.55) Thin Film Semiconductor ", Ferroelectrics, 2013 Publication	<1 %

---

Exclude quotes Off

Exclude matches Off

Exclude bibliography On